

7th All-Russian Conference “Gallium, aluminum and indium nitrides”

First announcement



Moscow State University
A.F.Ioffe Physico-Technical Institute
Russian Academy of Science

February 1– 3, 2010

Moscow, Russia

nitrides-conf.ioffe.ru

First announcement

The 7-th All-Russian Conference “Nitrides of gallium, indium and aluminum: structures and devices” organized by Moscow State University will be held in Moscow on February 1-3, 2010.

The annual Russian Conference on Gallium, Aluminum and Indium Nitrides organized for the first time in 1997 as a workshop aims to bring together scientific groups working in the field of III-nitrides in Russia. Despite the national character of the Russian III-N conference series, participants from all over the world are welcome.

Scope:

The scientific program will consist of invited talks, contributed talks, and poster presentations and cover following topics:

- Bulk material growth and substrates for III-N epitaxial growth.
- Epitaxial growth.
- Optical, electronic and structural properties of III-N materials.
- Properties of quantum-size structures based on III-N.
- Post-growth of III-N materials.
- Electronic and photoelectronics devices.
- Nitride based LEDs and LDs.
- Special session: Energy saving lighting.

The official language of III-N 2010 is Russian but some presentations may be done in English.

**If you are planning to attend the Conference,
please, contact Organizing Committee by e-mail:
[Nitrides2010 @ mail.ioffe.ru](mailto:Nitrides2010@mail.ioffe.ru) as soon as possible.**

More information can be found on conference web-site:
<http://nitrides-conf.ioffe.ru/>

Exhibition

A large hall will host the technical exhibits and the poster sessions, providing ample occasions for contacts between scientists and companies active in the field. If you are interested in advertising your company, products or services, or in sponsoring the conference, please contact the Organizing Committee.

Abstracts submission

Authors are invited to submit abstracts (2 pages for contribute and 4 pages for invited presentations) by e-mail:

[Nitrides2010 @ mail.ioffe.ru](mailto:Nitrides2010@mail.ioffe.ru) before December 1, 2009.

<http://nitrides-conf.ioffe.ru/abstractsinstructions.en.html>

Guidelines for abstract preparation.

Sample file in MS Word format can be downloaded from web site:
http://nitrides-conf.ioffe.ru/Sample_thesis_english.doc

The deadline for Abstracts submission is December 1, 2009

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